

53. (New) The device of claim 18 wherein said aluminum layer has a smaller resistivity than said refractory metal layer.

54. (New) The device of claim 18 further comprising an interlayer dielectric comprising a material selected from the group consisting of silicon nitride and silicon oxide provided over said interconnect and said thin film transistor.

55. (New) The device of claim 18 wherein said aluminum layer has a thickness of 6000 to 10000 A.

REMARKS

Reconsideration and allowance of the above referenced application are respectfully requested.

Figures 2A-2F are labeled herein as "prior art" to obviate the rejection.

The drawings also stand objected to under Rule 83a. The new claims obviate this rejection.

The rejection's suggested title has been adopted herein.

Claims 1, 2 and 4 stand rejected over the admitted prior art in view of Havemann. Claims 3, 5 and 6 stand rejected over the above combination in view of McDavid. In response, the

original claims are canceled herewith, and new claims replace those originally-created claims.

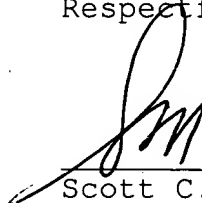
New claims 13-55 define that a metal layer or interconnect is formed in direct contact with a gate electrode. Because no interlayer dielectric is used to form this contact, a relatively small contact area becomes sufficient. The cited references do not teach or suggest this structure. Therefore, it is respectfully suggested that all of these claims should be in condition for allowance.

In view of the above amendments and remarks, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 11/23/99



Scott C. Harris
Reg. No. 32030

Attachment: Proposed drawing changes to Figures 2A-2F

Fish & Richardson P.C.
4225 Executive Square, Suite 1400
La Jolla, CA 92037
Telephone: (858) 678-5070
Facsimile: (858) 678-5099

10005662.doc